## Irradiation test of ABCStar ASICs in CSNS

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On behalf of ATLAS ITk Chinese group

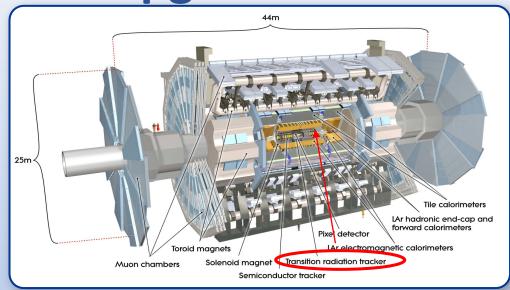
CLHCP 2023, Shanghai

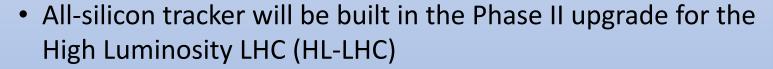


#### **Outline**

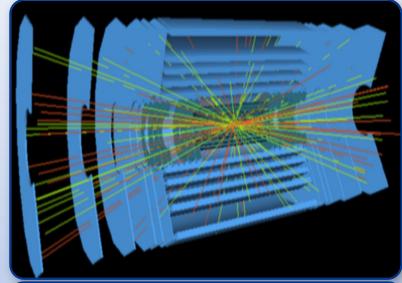
- Introduction
- ABCStar V1 chip, SEEs and TID
- CSNS irradiation
- Results from proton tests
- Preliminary conclusion

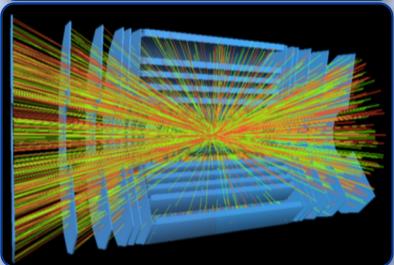
Phase II upgrade of ATLAS Inner Tracker for HL-LHC





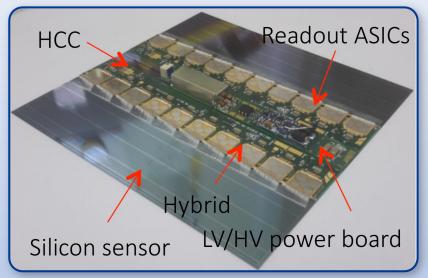
 The new detector will maintain or improve the current ATLAS tracking performance (ITk) to cope with the irradiation levels of the HL-LHC

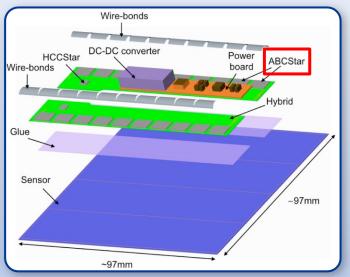


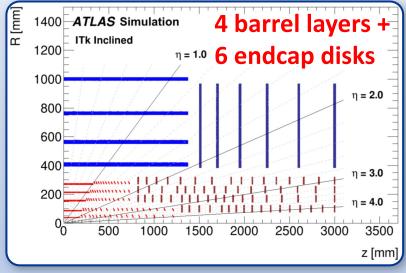


## **Inner Tracker (ITk)**

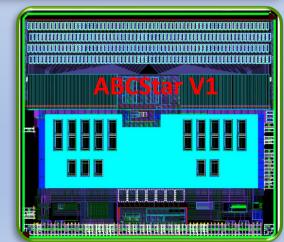
#### IHEP/THU contribute to the barrel of strip detector







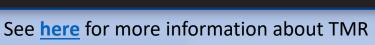
Strip detector comparisons	Current Inner strip tracker (SCT)	Future ITK strip tracker
Radial distance	300-560mm	400-1000mm
Channels	~8 millions	~100 millions
Modules	4 thousands	~20 thousands (165m² silicon)

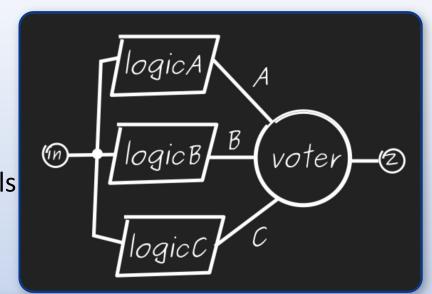


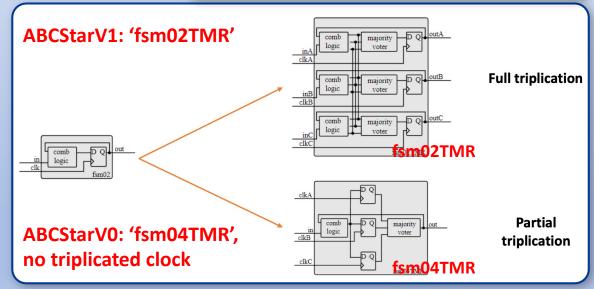
#### **ABCStar V1** specification

- $8 \text{ mm} \times 7 \text{ mm}$
- Fabricated using 130 nm CMOS technology
- Read out signals from 256 sensor strips by binary readout channels
- Triple Modular Redundancy (TMR)
  - Protect against SEEs

TMR Variants					
		Triplicated Registers	Triplicated Registers + clock skew	Full TMR	
Resoures (power, area)	FF	<i>x3</i>	<i>x3</i>	<i>x3</i>	
	logic	x1	x1	<i>x3</i>	
	voters	<i>x1</i>	x1	<i>x3</i>	
	clocks	x1	<i>x3</i>	<i>x3</i>	
Speed		+voter delay	+voter delay +clock skew	+voter delay	
Protection		•••	•••		

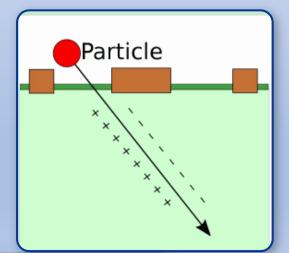


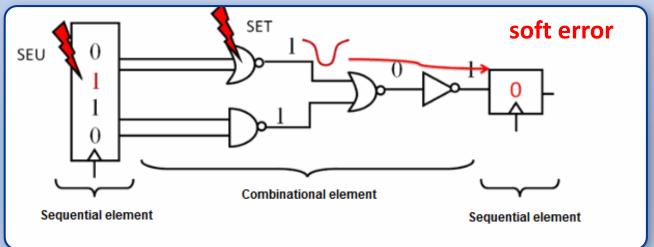




#### **SEEs**

- Single Event Effects (SEEs) electrical disturbance of an electronic device interacts with high-energy particle
  - Single Event Upset (SEU) affects both dynamic and static memory registers storing logic states by collecting charge → voltage change → bit flips happen
  - Single Event Transient (SET) a transient pulse produced by a charged particle in a circuit
    - → temporal disorder → bit flips happen





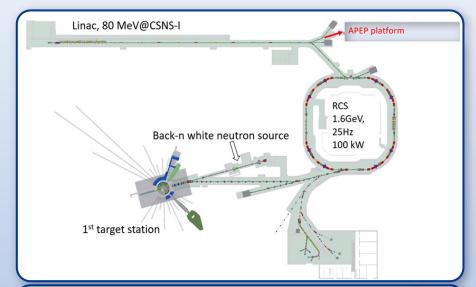


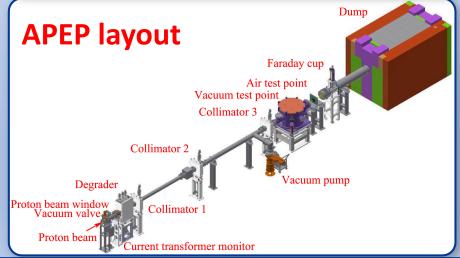
## **Total Ionzing Dose (TID)**

- An increase in digit current when chips exposed to ionizing doses of radiation
- Up to approximately 1 Mrad
- Continued exposure gradually reduces the current back towards normal value
- Refers to the cumulative amount of radiation
- The sensitivity of microelectronics to TID can impact reliability and functionality

## Proton beam at China Spallation Neutron Source (CSNS)

- We utilize the Associated Proton Experimental Platform (APEP platform) to have irradiation on ABCStar chips at the end of the CSNS linac
- To validate the performance of ABCStar ASICs V1 and V0, irradiated 2 campaigns:
  - May 2022: 80MeV, one V0 chip
  - April 2023: 20MeV ~ 80MeV, four V1 chips
- Beam spot → 20mm × 20mm
- Flux:  $1.16 \times 10^7 \rightarrow 2.66 \times 10^9 \text{ p/cm}^2/\text{s}$
- Fluence:  $1.24 \times 10^{14} \rightarrow 3.63 \times 10^{14} \text{ p/cm}^2$
- Dose: ~ 40 Mrad
- ~ 170 hours totally









#### **ABCStar beam test**

- ABCStar V1 chips under the same energy undergo different running scenarios
  - Clock disable (disabling one of the triplicated clocks)
  - Glitch Filter(delay incoming signal 1.3 ns)
  - BCID(one mode of filling the ABCStar's event data)
    - More realistic approximation of real event data
  - Idle(repeating binary data "0110" instead of "0000")
  - Latency 20/503(the data is stored in the ABCStar buffer for a period of time)
- Why we set diffent energy to have irradiation?
  - Linear Energy Transfer (LET) is not same at different energies



### Cross section (XS) of SEU

$$\sigma_{SEU} = \frac{n_{0\to 1} + n_{1\to 0}}{\int d\phi}$$

 $n_{0\to 1}$  and  $n_{1\to 0}$  are the number of  $0\to 1$  and  $1\to 0$  bit flips

The cross section is normalized to the total integrated fluence

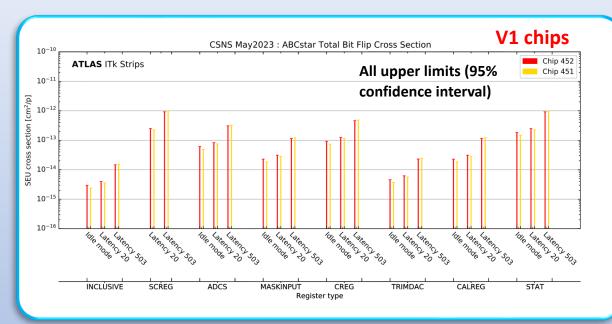
$$\Delta \sigma_{SEU} = 1.96 \times \frac{\sqrt{n_{0\to 1} + n_{1\to 0}}}{\int d\phi}$$

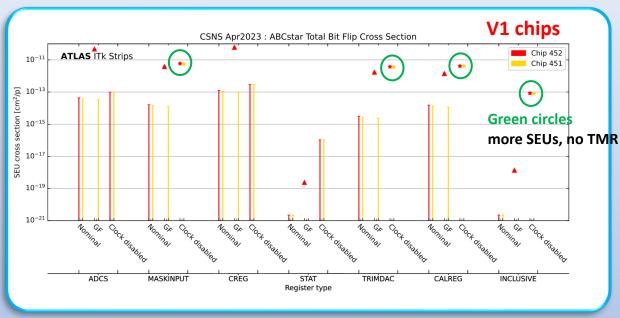
In the case of zero measured SEUs, 95% upper confidence bound is calculated

by assuming 3 SEUs

(Poisson statistics distribution)

#### SEE XS of registers with different modes



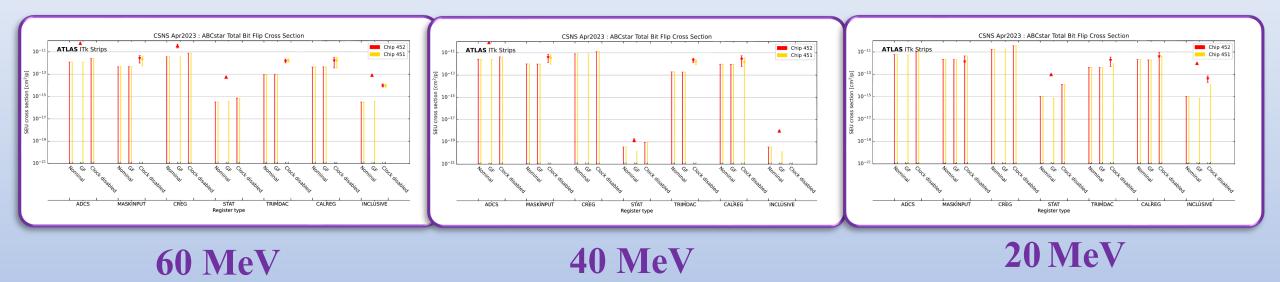


80 MeV 80 MeV

- If the cross section dependence on the data latency in buffer? No
- TMRs do enhance the irradiation hardness of ABCStar chips to SEE



#### SEE XS of registers at different energies



- Bit flips still happen with a certain probability when lower energy (20MeV)
- LET result in variations of the XS at different energies
- XS does not exhibit a clear pattern of variation with energy for the same register under the same mode

#### **TID** results

(1.8Mrad, 80mA) (1.40Mrad, 121.7mA) CSNS Apr 2023: FMC1701 IDDD All Chips CSNS Apr2023: FMC1701 IDDD All Chips Chip 452 (pre-irradiated) Chip 456 (pre-irradiated) 120 Chip 451 (pre-irradiated) Chip 454 (pre-irradiated) 70 100 -(1.38Mrad, 104.55mA) 60 [WM] QQQI DDD [mA] 30 40 20 dose rate = 146.5128(rads/s)dose rate = 293.0256(rads/s)80 MeV 20 dose rate=293.0256(rads/s) 10

Different dose rate is utilized at the same energy

20

Dose [Mrad]

30

40

10

• TID bump appears at around 1 Mrad as expected and pertains to the irradiation history

20

5

10

Dose [Mrad]

15

#### **Preliminary conclusion**

- SEE irradiation test about ABCStars have been performed at the APEP in CSNS.
- ABCStar V1 in which more TMR are implemented are more radiation hard as expected.
  - Register, logic of data transition, clocks
- The analysis of SEE cross section in physics packets is ongoing

# Thank you!

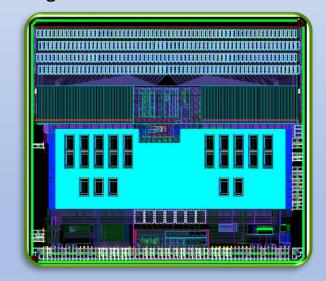


## backup

- The binary outputs produced by each front-end channel are captured and retained in the chip's Level 0 Buffer(LO\_Buffer)
- The ABCStar architecture supports a multi-trigger data flow
  - L0 trigger (L0A, with L0tag added): event data from the beam crossing synchronous pipeline (L0Buffer) is copied to the EventBuffer memory
  - LP (Low Priority) trigger: a first asynchronous readout request with priority and low latency for fast processing of track information
  - PR (Priority Request) trigger: A second asynchronous readout request intended for a global readout

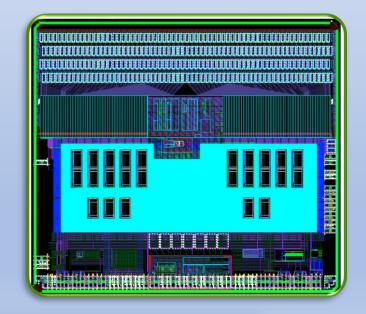
#### ABCStar V1(compared to V0) new modes

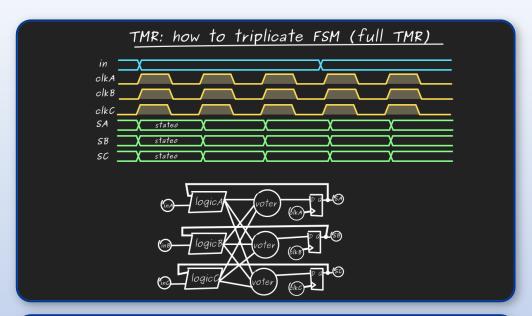
- SEU counter (8-bit)
  - Increases when a SEU is encountered in the registers: ADCS0, ADCS1, ADCS2, CREG0, CREG1
  - Not indicate register errors, but the occurrence of an upset and a subsequent corrective action
- Clock disabling
  - Disabling one of the triplicated clocks effectively increases the cross-section by a factor of 2
- Glitch filter
  - Delay a copy of the incoming signal by 1.3 ns and compares the copy with the original
  - The signal is not propagated further if they do not match
- Idle pattern
  - Programmable pattern (repeating "0110", default "0000")
- Latency setting(Latency 20/503, more SEUs)
  - Data is stored for some period of time awaiting a trigger
- Programmable multiplexer
  - Allows external output pin ("TESTOUT") to reflect internal signals inside ASICs
- Packet structure
  - 68 bits
  - Difference exists between V1 and V0, see <a href="here">here</a>

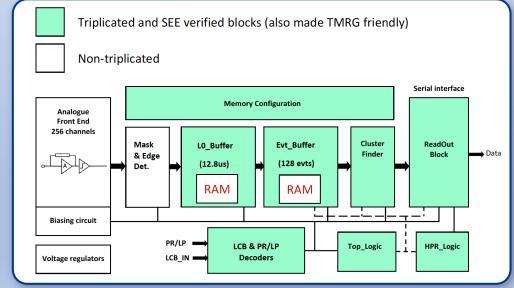


#### **ABCStar V1** specification

- 8 mm × 7 mm
- Fabricated using 130 nm CMOS technology
- Designed to read out signals from 256 sensor strips through binary readout channels
- Triple Modular Redundancy (TMR)







#### **ABCStar beam test**







### **Cross-section (XS) of SEE**

**XS** = (total number of occurences) / (total integrated fluence)

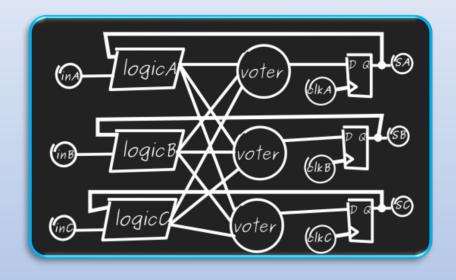
• For a nonzero number of occurences, a 95% confidence interval can be determined as follows:

 $\sigma(XS) = 1.96 \times \sqrt{\text{(total number of occurences)}} / \text{(total integrated fluence)}$ 



#### Register read XS

- Registers store configuration and counters
  - V1 chips have fully triple modular redundancy (TMR) (mitigate SEUs)
  - V0 chips don't have fully TMR
- Bit flips can be counted by comparing the expected register bits with the measured during repeatly readout



More information about TMR see <a href="here">here</a>, the image is from Stefan Biereigel and Szymon Kuli

